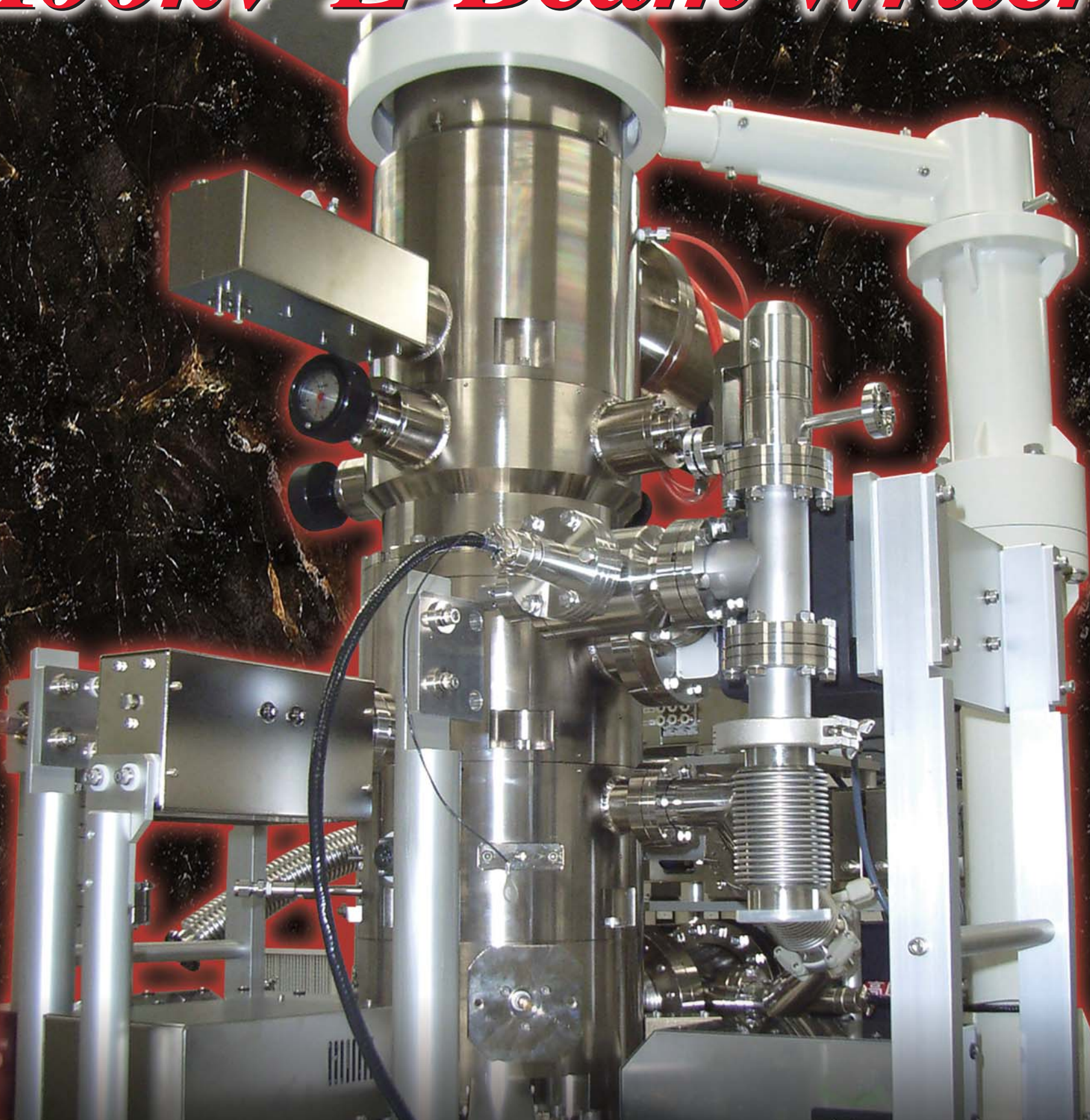


# *High Voltage Electron Beam Column for 100kV E-Beam Writer*



## **Electron Column**

Electron Source..... ZrO/W  
 Beam Energy..... 50, 100keV  
 Beam Shape..... Gaussian Spot Beam  
 Beam Current..... Up to 100nA  
 Imaging Area..... 500 $\mu$ m ~ 0.5 $\mu$ m  
 Min. Line Width..... 10nm at 5nA, 100kV  
 Electron Optics..... 3-lens Optics  
 Emitter Protection .. Built-in

## **Beam Blanker and Amplifier**

(Optional unit for EB recorder and writer)

Rise-up and Fall-down...<4nsec  
 Repetition Frequency...>30MHz

## **Deflection Units and Amplifiers**

(Optional unit for EB writer)

Main Deflection..... 20bit  $\leq$  500nsec (FS/32)  
 Sub Deflection..... 14bit  $\leq$  40nsec (FS/4)

Specifications are subject to change without notice.